

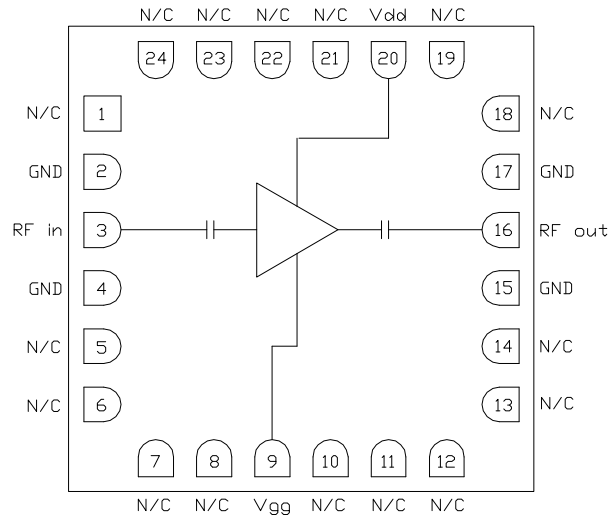
Features

- ▶ High gain
- ▶ Low noise figure
- ▶ High linearity
- ▶ High RF power survivability
- ▶ Pb-free RoHs compliant 4x4 QFN package

Description

The CMD276C4 is a broadband MMIC GaN low noise amplifier housed in a leadless 4x4 mm QFN package. The CMD276C4 is ideally suited for microwave radios and S-band applications where small size and high input power survivability are needed. The broadband device delivers greater than 14 dB of gain with a corresponding output 1 dB compression point of +25.5 dBm and a noise figure of 1.2 dB. The CMD276C4 features an RF input power survivability of greater than 5 Watts.

Functional Block Diagram



Electrical Performance – $V_{dd} = 10\text{ V}$, $I_{dd} = 225\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$, $F = 3.5\text{ GHz}$

| Parameter | Min | Typ | Max | Units |
|--------------------|---------|------|-----|-------|
| Frequency Range | 2.6 – 4 | | | GHz |
| Gain | | 14.5 | | dB |
| Noise Figure | | 1.2 | | dB |
| Output P1dB | | 25.5 | | dBm |
| Output Psat | | 28 | | dBm |
| Output IP3 | | 32 | | dBm |
| Input Return Loss | | -9.5 | | dB |
| Output Return Loss | | -13 | | dB |
| Supply Current | | 225 | | mA |

ver 1.2 0219



CMD276C4

2.6-4 GHz GaN Low Noise Amplifier

Specifications

Absolute Maximum Ratings

| Parameter | Rating |
|--------------------------------------|---------------|
| Drain Voltage, V _{dd} | 35 V |
| RF Input Power (CW or pulsed) | 5 W |
| Channel Temperature, T _{ch} | 200 °C |
| Power Dissipation, P _{diss} | 3.55 W |
| Thermal Resistance, Θ_{JC} | 18.3 °C/W |
| Operating Temperature | -40 to 85 °C |
| Storage Temperature | -55 to 150 °C |

Exceeding any one or combination of the maximum ratings may cause permanent damage to the device.

Recommended Operating Conditions

| Parameter | Min | Typ | Max | Units |
|-----------------|-----|------|------|-------|
| V _{dd} | 5 | 10 | 28 | V |
| I _{dd} | | 225 | | mA |
| V _{gg} | -4 | -1.5 | -0.7 | V |

Electrical performance is measured at specific test conditions. Electrical specifications are not guaranteed over all recommended operating conditions.

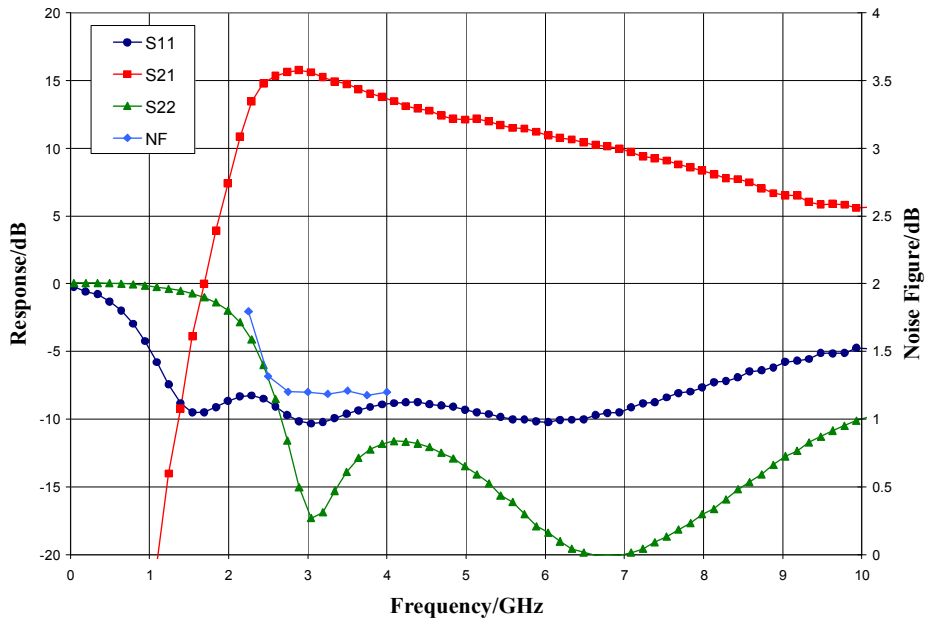
Electrical Specifications – V_{dd} = 10 V, I_{dd} = 225 mA, T_A = 25 °C

| Parameter | Min | Typ | Max | Units |
|--------------------------------------|---------|-------|-----|-------|
| Frequency Range | 2.6 – 4 | | | GHz |
| Gain | 11 | 14.5 | 19 | dB |
| Noise Figure | | 1.2 | 2 | dB |
| Input Return Loss | | -9.5 | | dB |
| Output Return Loss | | -13 | | dB |
| Output P _{1dB} | | 25.5 | | dBm |
| Output IP ₃ | | 32 | | dBm |
| Supply Current | 158 | 225 | 292 | mA |
| Gain Temperature Coefficient | | 0.01 | | dB/°C |
| Noise Figure Temperature Coefficient | | 0.006 | | dB/°C |

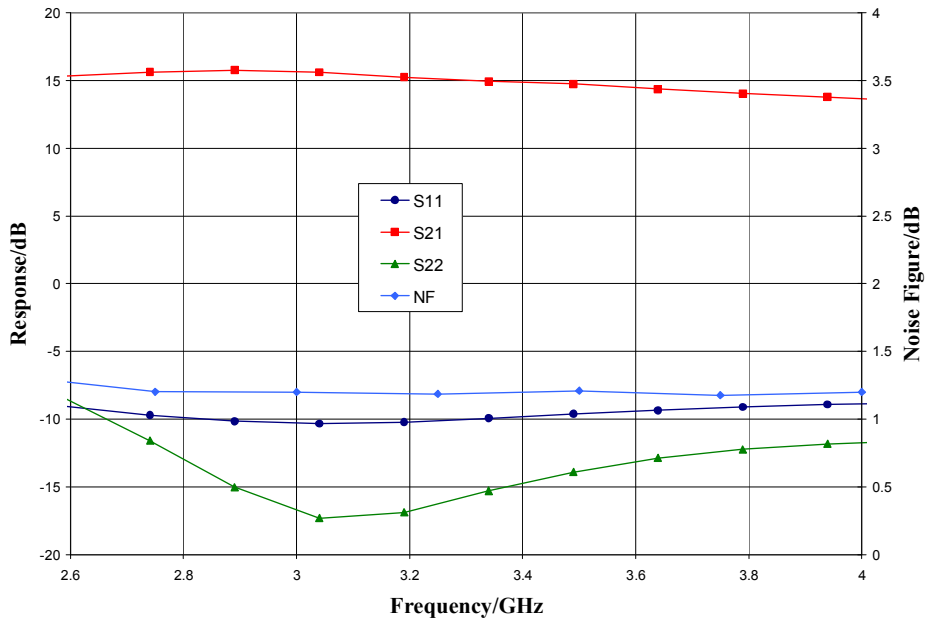
ver 1.2 0219

Typical Performance

Broadband Performance, $V_{dd} = 10\text{ V}$, $I_{dd} = 225\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



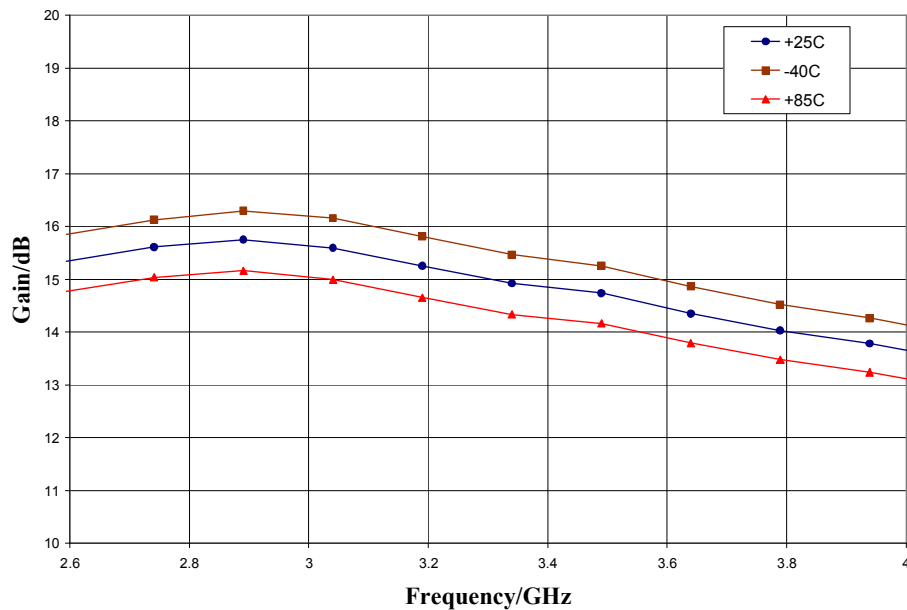
Narrow-band Performance, $V_{dd} = 10\text{ V}$, $I_{dd} = 225\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



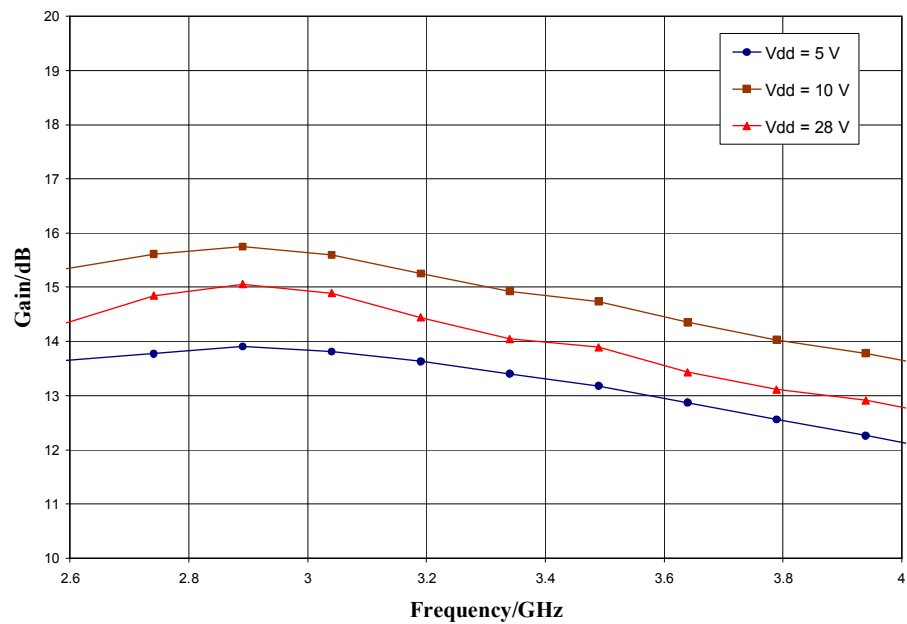
ver 1.2 0219

Typical Performance

Gain vs. Temperature, $V_{dd} = 10\text{ V}$



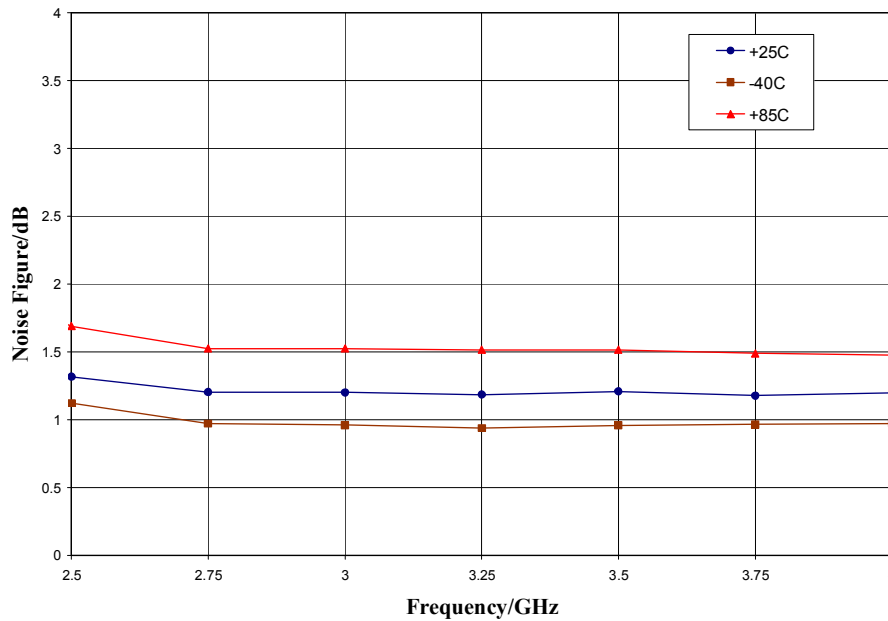
Gain vs. V_{dd} , $I_{dd} = 225\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



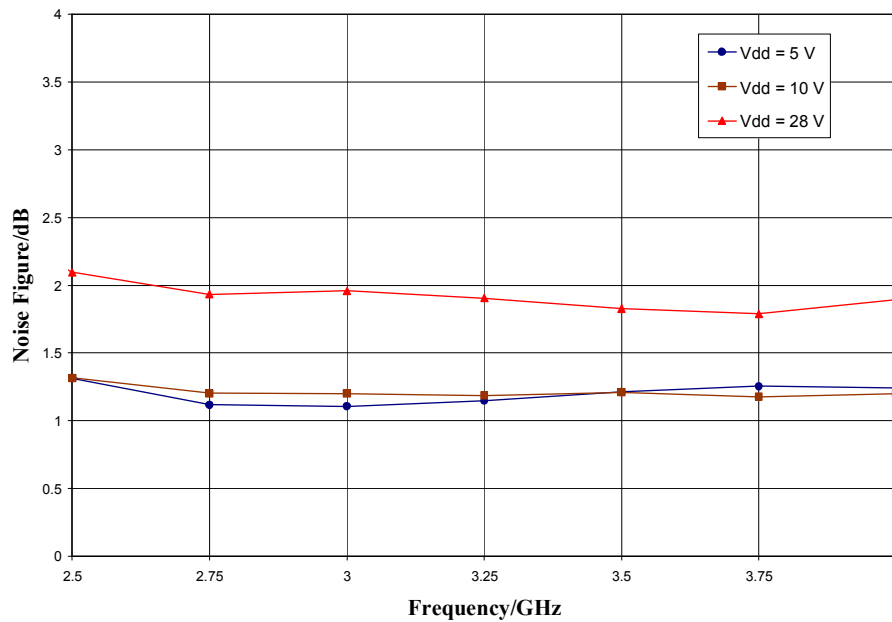
ver 1.2 0219

Typical Performance

Noise Figure vs. Temperature, $V_{dd} = 10\text{ V}$



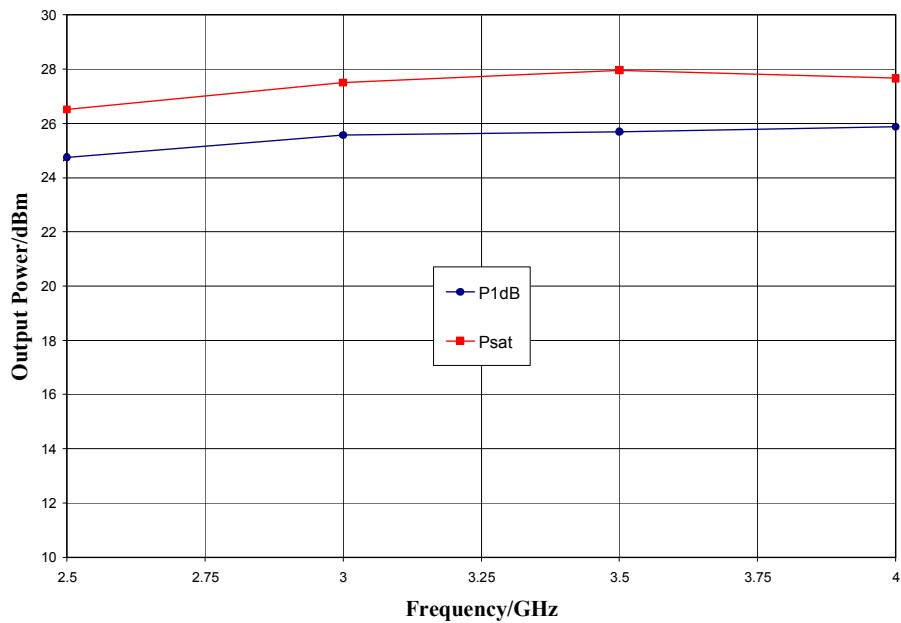
Noise Figure vs. V_{dd} , $I_{dd} = 225\text{ mA}$, $T_A = 25\text{ }^\circ\text{C}$



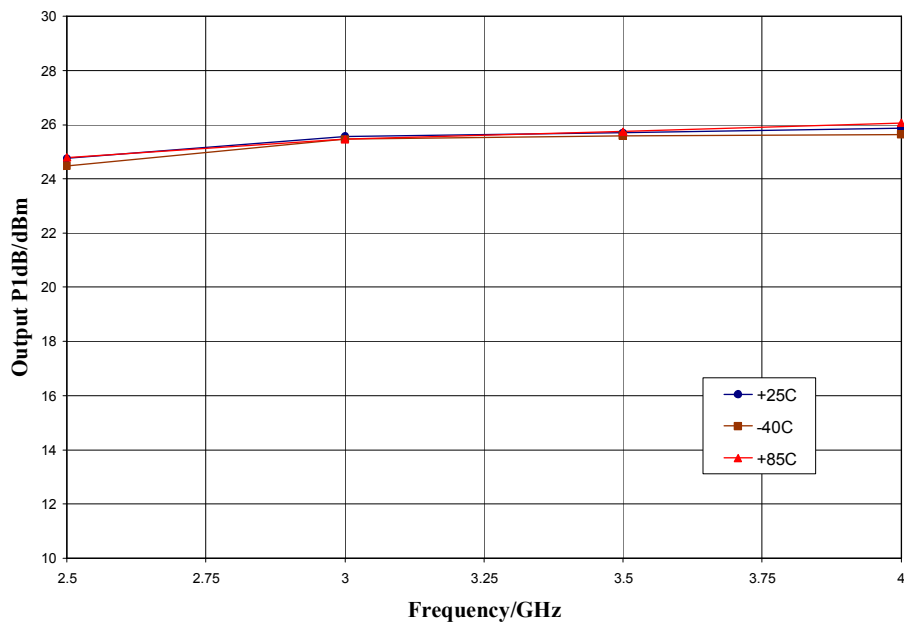
ver 1.2 0219

Typical Performance

Output Power, $V_{dd} = 10\text{ V}$, $T_A = 25\text{ }^\circ\text{C}$



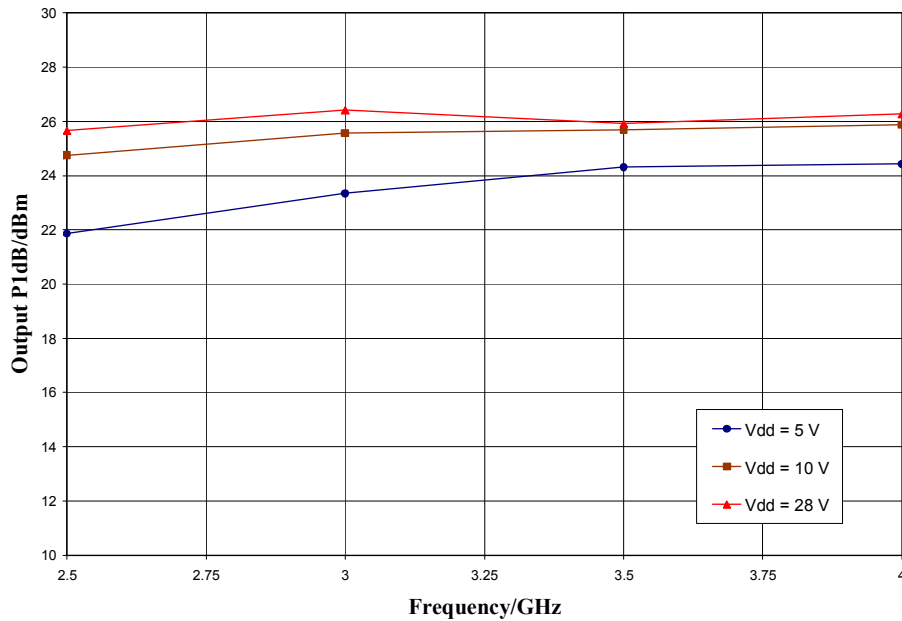
P1dB vs. Temperature, $V_{dd} = 10\text{ V}$



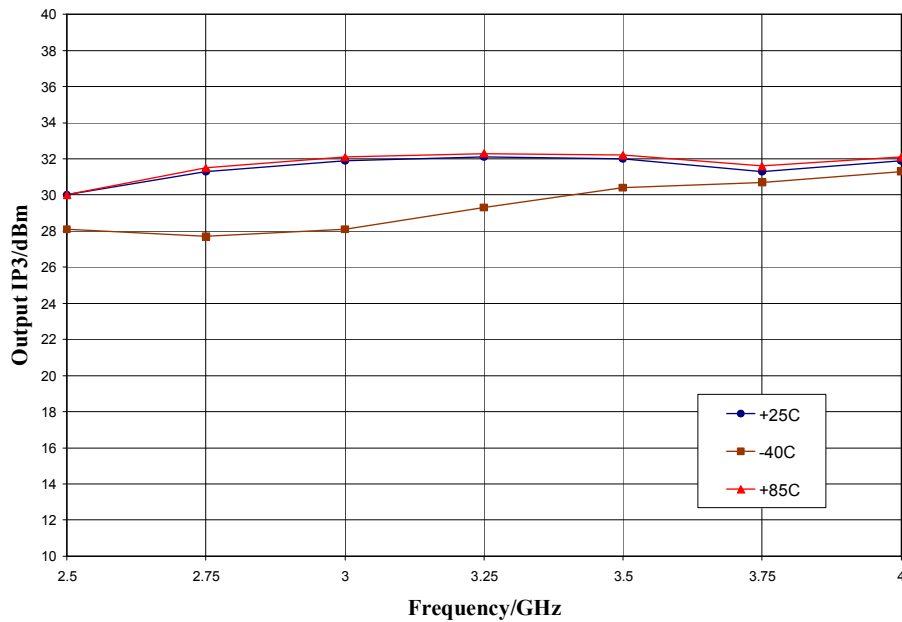
ver 1.2 0219

Typical Performance

P1dB vs. V_{dd} , $T_A = 25^\circ\text{C}$



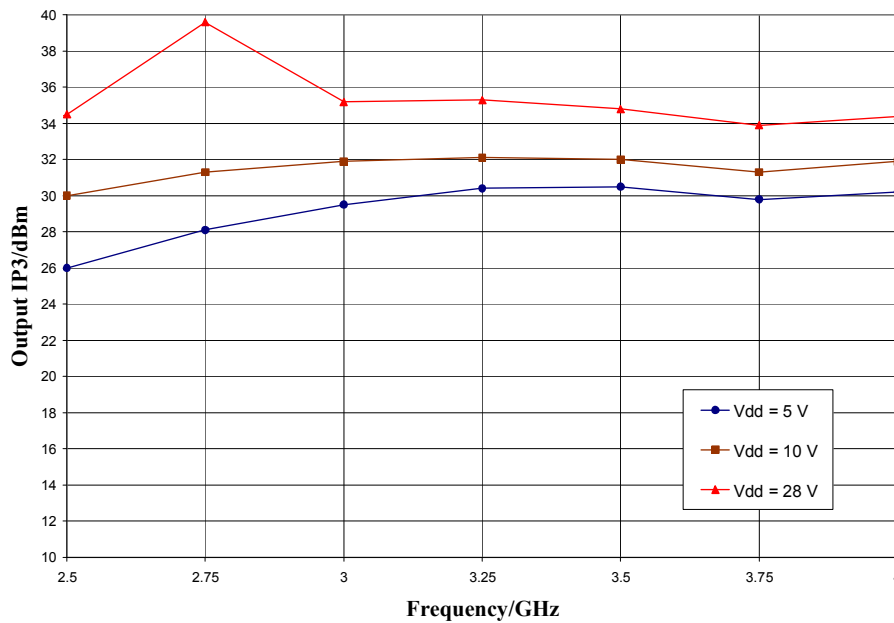
Output IP3 vs. Temperature, $V_{dd} = 10\text{ V}$



ver 1.2 0219

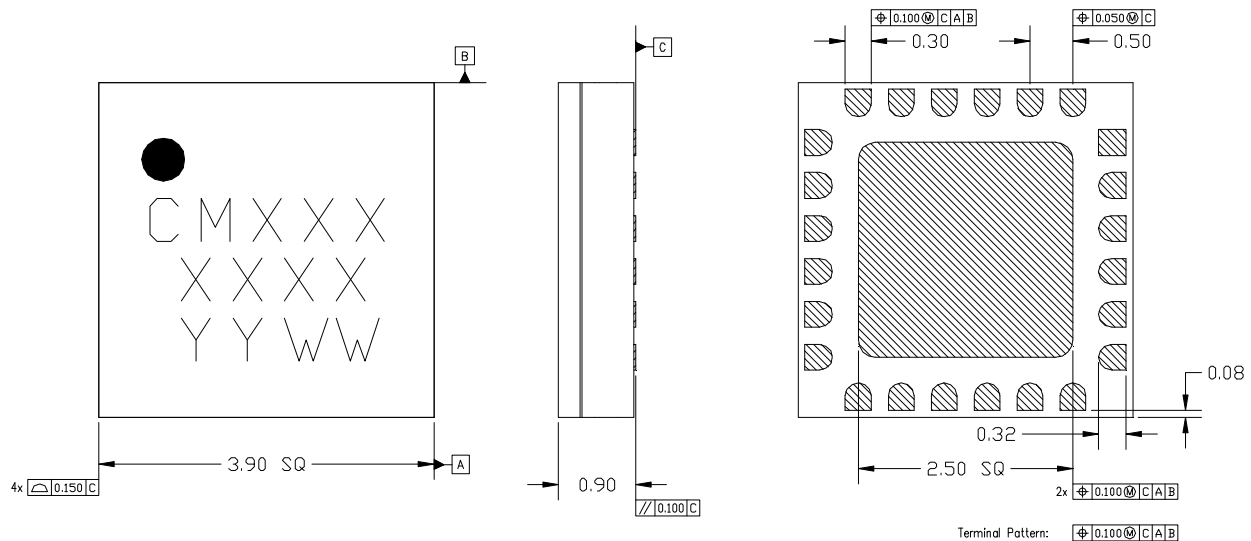
Typical Performance

Output IP3 vs. V_{dd} , $I_{dd} = 225$ mA, $T_A = 25$ °C



Mechanical Information

Package Information and Dimensions



- NOTES:
1. ALL DIMENSIONS SHOWN IN mm.
 2. MATERIAL: BLACK ALUMINA
 3. LEAD FINISH:
 - 3.1. Ni: 8.89um MAX, 1.27um MIN
 - 3.2. Pd: 0.17um MAX, 0.07um MIN
 - 3.3. Au: 0.254um MAX, 0.03um MIN
 4. MARKING
 - 4.1. LINE 1: PART NUMBER
 - 4.1.1. EXAMPLE: CMD191C4 SHALL BE MARKED AS CM191
 - 4.2. LINE 2: LOT NUMBER
 - 4.3. LINE 3: DATE CODE - LAST 2 DIGITS OF THE YEAR OF MANUFACTURE FOLLOWED BY A 2 DIGIT WEEK CODE
 5. ALTERNATE PIN #1 IDENTIFIER IS A SINGLE SQUARE PAD
 6. ALTERNATE DIE PADDLE MAY HAVE CHAMFERED CORNERS

Recommended PCB Land Pattern

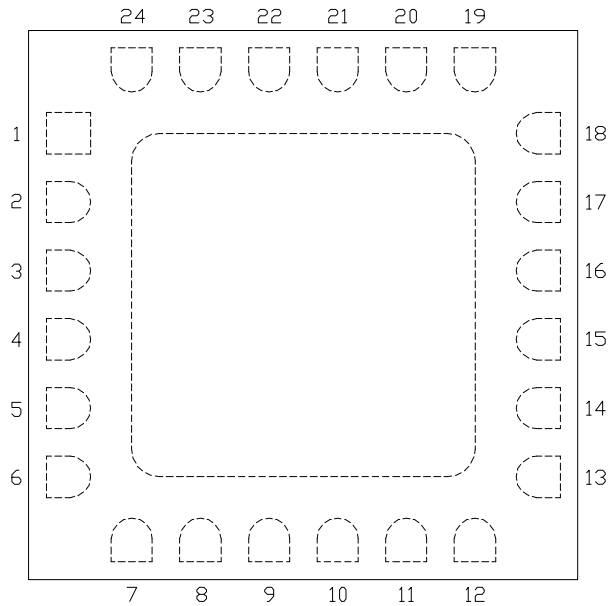
Custom MMIC Design Services recommends that the user develop the land pattern that will provide the best design for proper solder reflow and device attach for their specific application. Please review Custom MMIC Application Note AN 105 for a recommended land pattern approach.

Recommended Solder Reflow Profile


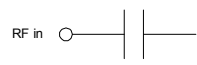
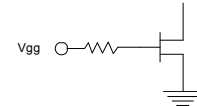

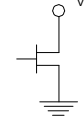
Custom MMIC Design Services recommends screen printing with belt furnace reflow to ensure proper solder reflow and device attach. Please review Custom MMIC Application Note AN 102 for a recommended solder reflow profile.

Pin Description

Pin Diagram



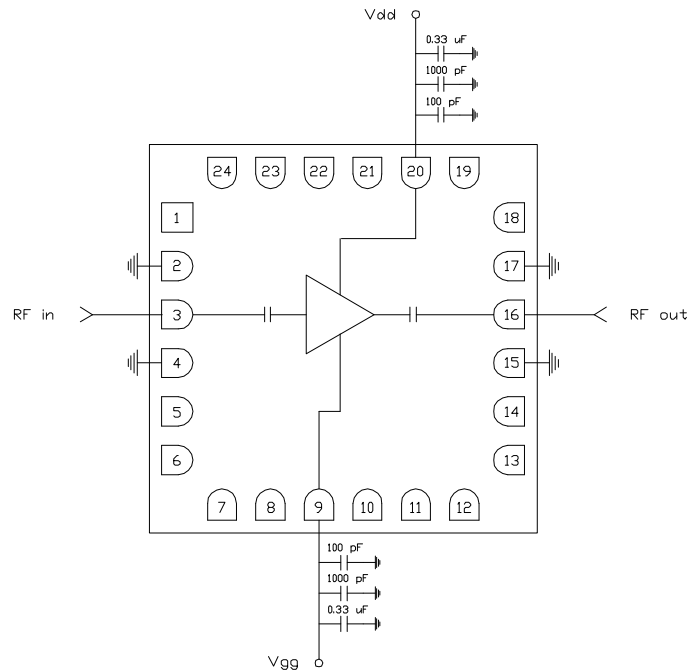
Functional Description

| Pin | Function | Description | Schematic |
|------------------------------|-----------------|---|---|
| 1, 5-8, 10-14, 18, 19, 21-24 | N/C | No connection required. These pins may be connected to RF/DC ground | |
| 2, 4, 15, 17 and die paddle | Ground | Connect to RF/DC ground |  |
| 3 | RF in | DC blocked and 50 ohm matched |  |
| 9 | V _{gg} | Power supply voltage Decoupling and bypass caps required |  |
| 16 | RF out | DC blocked and 50 ohm matched |  |
| 20 | V _{dd} | Power supply voltage Decoupling and bypass caps required |  |

ver 1.2 0219

Applications Information

Application Circuit



Biasing and Operation

The CMD276C4 is biased with a positive drain supply and a negative gate supply. Performance is optimized when the drain voltage is set to +10 V but may be set between +5 V and +28 V.

Turn ON procedure:

1. Apply gate voltage V_{gg} and set to a voltage sufficient to pinch off drain current (~ -4 V)
2. Apply drain voltage V_{dd} and set to +10 V
3. Increase V_{gg} (less negative) to achieve a drain current of 225 mA

Turn OFF procedure:

1. Turn off drain voltage V_{dd}
2. Turn off gate voltage V_{gg}

RF power can be applied at any time

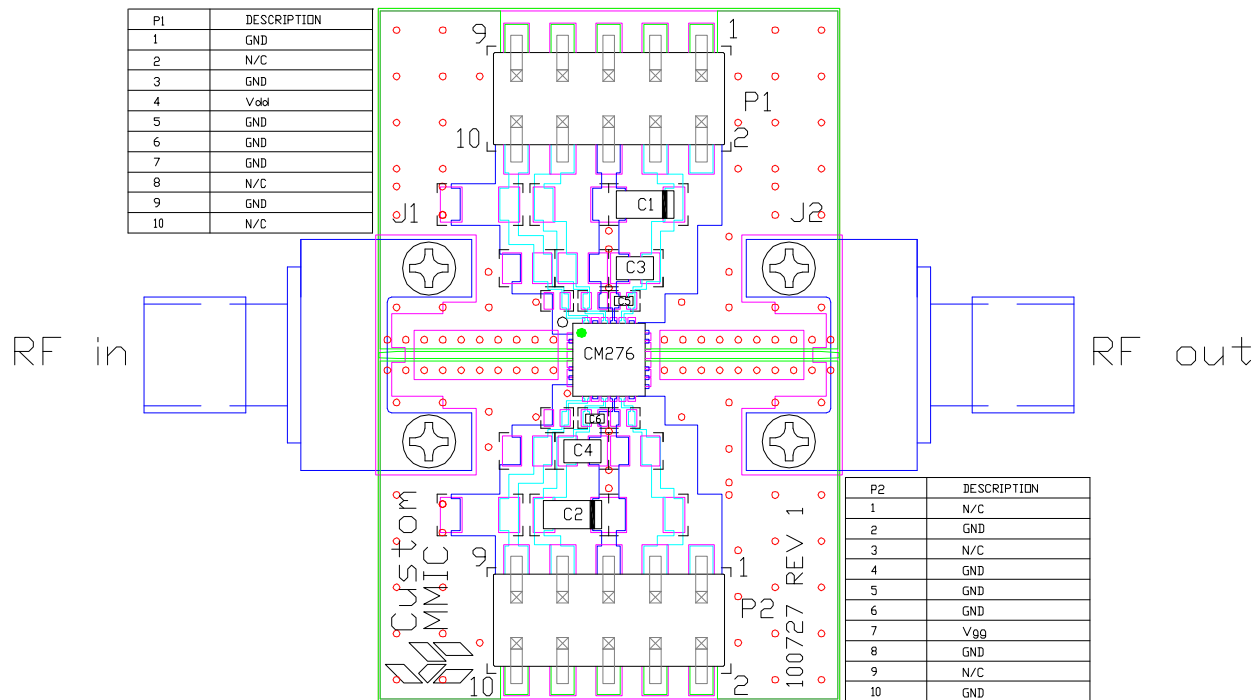
GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

ver 1.2 0219

Applications Information

Evaluation Board

The circuit board shown has been developed for optimized assembly at CMDS. A sufficient number of via holes should be used to connect the top and bottom ground planes. As surface mount processes vary, careful process development is recommended.



Bill of Material

| Designator | Value | Description |
|------------|--------------|------------------------------|
| J1, J2 | | SMA End Launch Connector |
| P1, P2 | | 10 Pin Header |
| C1, C2 | 0.33 μ F | Capacitor, Tantalum |
| C3, C4 | 1000 pF | Capacitor, 0603 |
| C5, C6 | 100 pF | Capacitor, 0402 |
| U1 | | CMD276C4 Low Noise Amplifier |
| PCB | | 100727 Evaluation PCB |

Please note, all information contained in this data sheet is subject to change without notice.

ver 1.2 0219